

# Hsien-Chin Chiu

## List of Publications by Year in descending order

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docs citations

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times ranked

1060  
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#	ARTICLE	IF	CITATIONS
1	1.3kV Vertical GaN-Based Trench MOSFETs on 4-Inch Free Standing GaN Wafer. Nanoscale Research Letters, 2022, 17, 14.	3.1	10
2	AlGaIn/GaN Schottky Barrier Diodes on Free-Standing GaN Substrates With a Si Doped Barrier Layer. IEEE Journal of the Electron Devices Society, 2022, 10, 318-323.	1.2	0
3	1.7-kV Vertical GaN-on-GaN Schottky Barrier Diodes With Helium-Implanted Edge Termination. IEEE Transactions on Electron Devices, 2022, 69, 1938-1944.	1.6	15
4	Improved Ion/Ioff Current Ratio and Dynamic Resistance of a p-GaN High-Electron-Mobility Transistor Using an Al <sub>0.5</sub> GaN Etch-Stop Layer. Materials, 2022, 15, 3503.	1.3	1
5	Hole Injection Effect and Dynamic Characteristic Analysis of Normally Off p-GaN HEMT with AlGaIn Cap Layer on Low-Resistivity SiC Substrate. Micromachines, 2022, 13, 807.	1.4	2
6	A 5-Bit X-Band GaN HEMT-Based Phase Shifter. Electronics (Switzerland), 2021, 10, 658.	1.8	6
7	Monolithic Integration of Strained UV-Visible Dual Color Photodetectors on 4 in. Multilayer MoS <sub>2</sub> -on-Freestanding GaN Wafer by Direct van der Waals Growth. ACS Applied Electronic Materials, 2021, 3, 1988-1995.	2.0	5
8	Effects of Thermal Annealing on the Properties of Zirconium-Doped Mg <sub>x</sub> Zn <sub>1-x</sub> O Films Obtained through Radio-Frequency Magnetron Sputtering. Membranes, 2021, 11, 373.	1.4	4
9	High Thermal Dissipation of Normally off p-GaN Gate AlGaIn/GaN HEMTs on 6-Inch N-Doped Low-Resistivity SiC Substrate. Micromachines, 2021, 12, 509.	1.4	5
10	Review of Recent Progress on Vertical GaN-Based PN Diodes. Nanoscale Research Letters, 2021, 16, 101.	3.1	34
11	Normally-Off p-GaN Gated AlGaIn/GaN MIS-HEMTs with ALD-Grown Al <sub>2</sub> O <sub>3</sub> /AlN Composite Gate Insulator. Membranes, 2021, 11, 727.	1.4	6
12	Improved Gate Reliability Normally-Off p-GaN/AlN/AlGaIn/GaN HEMT With AlGaIn Cap-Layer. IEEE Electron Device Letters, 2021, 42, 1432-1435.	2.2	13
13	The Characteristics of 6-Inch GaN on Si RF HEMT with High Isolation Composited Buffer Layer Design. Electronics (Switzerland), 2021, 10, 46.	1.8	4
14	Characteristic Analysis of AlGaIn/GaN HEMT with Composited Buffer Layer on High-Heat Dissipation Poly-AlN Substrates. Membranes, 2021, 11, 848.	1.4	4
15	Fabrication of Inkjet-Printed Carbon Nanotube for Enhanced Mechanical and Strain-Sensing Performance. ECS Journal of Solid State Science and Technology, 2021, 10, 121001.	0.9	1
16	Analysis of the back-barrier effect in AlGaIn/GaN high electron mobility transistor on free-standing GaN substrates. Journal of Alloys and Compounds, 2020, 814, 152293.	2.8	23
17	Electromagnetic Induced Failure in GaN-HEMT High-Frequency Power Amplifier. IEEE Transactions on Industrial Electronics, 2020, 67, 5708-5716.	5.2	6
18	Mechanical tensile strain for AlGaIn/GaN metal-insulator-semiconductor high-electron-mobility transistors on a silicon-on-insulator substrate. Journal of Alloys and Compounds, 2020, 820, 153178.	2.8	2

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19	150â€“200 V Split-Gate Trench Power MOSFETs with Multiple Epitaxial Layers. <i>Micromachines</i> , 2020, 11, 504.	1.4	4
20	High Threshold Voltage Normally off Ultra-Thin-Barrier GaN MISHEMT with MOCVD-Regrown Ohmics and Si-Rich LPCVD-SiNx Gate Insulator. <i>Energies</i> , 2020, 13, 2479.	1.6	1
21	Normally-off p-GaN Gated AlGaIn/GaN HEMTs Using Plasma Oxidation Technique in Access Region. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 229-234.	1.2	22
22	ZnO UV Photodetectors Modified by Ag Nanoparticles Using All-Inkjet-Printing. <i>Nanoscale Research Letters</i> , 2020, 15, 176.	3.1	42
23	Low Gate Lag Normally-Off p-GaN/AlGaIn/GaN High Electron Mobility Transistor with Zirconium Gate Metal. <i>Crystals</i> , 2020, 10, 25.	1.0	4
24	High-Frequency Electromagnetic Simulation and Optimization for GaN-HEMT Power Amplifier IC. <i>IEEE Transactions on Electromagnetic Compatibility</i> , 2019, 61, 564-571.	1.4	15
25	The Demonstration of Recessed Anodes AlGaIn/GaN Schottky Barrier Diodes Using Microwave Cyclic Plasma Oxidation/Wet Etching Techniques. , 2019, , .		1
26	Vertical GaN-on-GaN PIN diodes fabricated on free-standing GaN wafer using an ammonothermal method. <i>Journal of Alloys and Compounds</i> , 2019, 804, 435-440.	2.8	13
27	The demonstration of recessed anodes AlGaIn/GaN Schottky barrier diodes using microwave cyclic plasma oxidation/wet etching techniques. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 071002.	0.8	5
28	GaN on Si RF Devices and MMICs-Pivotal Driving Force of 5G Communication Micro/Macro Cells. , 2019, , .		2
29	A Low Impact Ionization Rate Poly-Si TFT with a Current and Electric Field Split Design. <i>Coatings</i> , 2019, 9, 514.	1.2	3
30	A $K_a$ -Band GaAs MMIC Traveling-Wave Switch With Absorptive Characteristic. <i>IEEE Microwave and Wireless Components Letters</i> , 2019, 29, 394-396.	2.0	23
31	Double-Gate Two-Step Source/Drain Poly-Si Thin-Film Transistor. <i>Coatings</i> , 2019, 9, 233.	1.2	3
32	Dynamic Behavior Improvement of Normally-Off p-GaN High-Electron-Mobility Transistor Through a Low-Temperature Microwave Annealing Process. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 984-989.	1.2	3
33	High-Performance Normally Off p-GaN Gate HEMT With Composite AlN/Al <sub>0.17</sub> Ga <sub>0.83</sub> N/Al <sub>0.3</sub> Ga <sub>0.7</sub> N Barrier Layers Design. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 201-206.	1.2	39
34	AlGaIn/GaN Schottky barrier diodes on silicon substrates with various Fe doping concentrations in the buffer layers. <i>Microelectronics Reliability</i> , 2018, 83, 238-241.	0.9	6
35	High Uniformity Normally-OFF p-GaN Gate HEMT Using Self-Terminated Digital Etching Technique. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4820-4825.	1.6	33
36	High Performance InAlN/GaN/Si High Electron Mobility Transistor Using Microwave Ohmic Annealing Technique. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, Q185-Q189.	0.9	1

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37	Reliability Studies on AlGaIn/GaN Metal-Insulator-Semiconductor High-Electron-Mobility Transistors with Through-Substrate via Technique and Backside Heat Sink Metal on Silicon-on-Insulator Substrates. ECS Journal of Solid State Science and Technology, 2018, 7, Q142-Q147.	0.9	3
38	2.4 kV Vertical GaN PN Diodes on Free Standing GaN Wafer Using CMOS-Compatible Contact Materials. IEEE Journal of the Electron Devices Society, 2018, 6, 825-829.	1.2	10
39	Fully Inkjet-Printed Dual-Mode Ring Bandpass Filter Using a Cross-Bridge Structure Embedded With a Metal-Insulator-Metal Capacitor. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2018, 8, 1869-1875.	1.4	3
40	A coupled-inductor dual-mode switched voltage-controlled oscillator using GaN-on-Si HEMT technology. International Journal of Electronics, 2017, 104, 228-237.	0.9	0
41	Improved reverse recovery characteristics of low turn-on voltage AlGaIn/GaN Schottky barrier diodes with anode edge AlON spacers. Journal of Alloys and Compounds, 2017, 703, 204-209.	2.8	3
42	A 60-GHz CMOS Frequency Tripler With Broadband Performance. IEEE Microwave and Wireless Components Letters, 2017, 27, 281-283.	2.0	27
43	A high output power and low phase noise GaN HEMT VCO with array of switchable inductors. International Journal of Circuit Theory and Applications, 2017, 45, 1621-1636.	1.3	1
44	Improved reverse recovery characteristics of InAlN/GaN schottky barrier diode using a SOI substrate. Semiconductor Science and Technology, 2017, 32, 105009.	1.0	2
45	RF Performance of <i>In Situ</i> Si <sub>x</sub> Gate Dielectric AlGaIn/GaN MISHEMT on 6-in Silicon-on-Insulator Substrate. IEEE Transactions on Electron Devices, 2017, 64, 4065-4070.	1.6	10
46	Effect of various Fe-doped AlGaIn buffer layer of AlGaIn/GaN HEMTs on Si substrate. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	9
47	The design of wideband transformer-coupled 90-nm CMOS power amplifier for V-band application. , 2017, , .		1
48	A <i>K</i> -band VCO with low phase noise and wide tuning range using a 90-nm dual-gate device. Microwave and Optical Technology Letters, 2016, 58, 502-505.	0.9	1
49	A broadband Darlington power amplifier using 0.5 Åµm GaN-on-SiC HEMT process. , 2016, , .		1
50	Miniaturized stub-loaded resonator bandpass filter fabricated using multilayer inkjet printing technology. , 2016, , .		2
51	A broadband 60 GHz CMOS up-converter design and analysis. , 2016, , .		2
52	Detection of pH and Enzyme-Free H <sub>2</sub> O <sub>2</sub> Sensing Mechanism by Using GdO <sub>x</sub> Membrane in Electrolyte-Insulator-Semiconductor Structure. Nanoscale Research Letters, 2016, 11, 434.	3.1	6
53	Physical properties of Al-doped MgZnO/AlGaIn p-n heterojunction photodetectors. Optical and Quantum Electronics, 2016, 48, 1.	1.5	2
54	A High-Current Kink Effect Free Z-Gate Poly-Si Thin-Film Transistor. IEEE Electron Device Letters, 2016, 37, 886-889.	2.2	4

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55	Inkjet-Printed Multilayer Bandpass Filter Using Liquid Crystal Polymer System-on-Package Technology. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2016, 6, 622-629.	1.4	8
56	A monolithic low phase noise power oscillator using 0.35 $\mu$ m GaN/Al <sub>0.27</sub> Ga <sub>0.73</sub> N MMIC process. International Journal of Electronics Letters, 2016, 4, 313-322.	0.7	4
57	A broadband and high power frequency tripler using 0.5 $\mu$ m GaN-on-SiC HEMT technology. , 2015, , .		0
58	Characterization of Nb-doped MgZnO films grown by a radio-frequency magnetron sputtering system. , 2015, , .		0
59	A Wide Tuning-Range CMOS VCO with a Tunable Active Inductor. Mathematical Problems in Engineering, 2015, 2015, 1-7.	0.6	10
60	Enhancement/Depletion-mode AlGaIn/GaN HEMTs demonstration using partial p-type GaN gate etching process. , 2015, , .		0
61	Microwave wide bandgap GaN high electron mobility transistor development and its monolithic integrated circuits (Invited). , 2015, , .		1
62	Analysis of the Back-Gate Effect in Normally OFF p-GaN Gate High-Electron Mobility Transistor. IEEE Transactions on Electron Devices, 2015, 62, 507-511.	1.6	23
63	Effects of the Fe-doped GaN buffer in AlGaIn/GaN HEMTs on SiC substrate. , 2015, , .		2
64	Bending Effect of an Inkjet-Printed Series-Fed Two-Dipole Antenna on a Liquid Crystal Polymer Substrate. IEEE Antennas and Wireless Propagation Letters, 2014, 13, 1172-1175.	2.4	26
65	V $\mu$ band GaAs low LO power driven double $\pi$ -balanced Gilbert mixer based on dual $\pi$ -meandering baluns design. Microwave and Optical Technology Letters, 2014, 56, 60-64.	0.9	0
66	Thermal stability of post-growth-annealed Ga-doped MgZnO films grown by the RF sputtering method. Materials Research Society Symposia Proceedings, 2014, 1675, 41-44.	0.1	0
67	Field-plated GaAs on Si substrate HEMT technology for microwave and power electronics applications (invited). , 2014, , .		1
68	High microwave power source for 2.45 $\mu$ GHz wireless power charger applications. International Journal of Electronics, 2014, 101, 469-478.	0.9	5
69	Inkjet Printed Series-Fed Two-Dipole Antenna Comprising a Balun Filter on Liquid Crystal Polymer Substrate. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2014, 4, 1228-1236.	1.4	26
70	A Novel Micromachined AlGaIn/GaN Power HEMT With Air-Bridged Matrix Heat Redistribution Layer Design. IEEE Electron Device Letters, 2014, 35, 163-165.	2.2	7
71	A F-band balanced power amplifier in 0.15 $\mu$ m GaAs pHEMT process. , 2014, , .		0
72	A wide bandwidth V $\mu$ band balanced resistive mixer with a miniature meandering balun. Microwave and Optical Technology Letters, 2013, 55, 547-550.	0.9	3

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73	V-band Push-Push VCO using Slow-Wave CPW Resonators for Low Phase Noise Reduction. Microwave and Optical Technology Letters, 2013, 55, 2373-2377.	0.9	1
74	High performance InAs/AlSb HEMT with refractory iridium Schottky gate metal. , 2013, , .		0
75	Characteristics of AlGaIn/GaN HEMTs With Various Field-Plate and Gate-to-Drain Extensions. IEEE Transactions on Electron Devices, 2013, 60, 3877-3882.	1.6	34
76	A high output power V-band GaAs HEMT push-pull power amplifier using meandering baluns technology. Journal of Electromagnetic Waves and Applications, 2013, 27, 1869-1881.	1.0	2
77	A Novel Self-Aligned Double-Channel Polysilicon Thin-Film Transistor. IEEE Transactions on Electron Devices, 2013, 60, 799-804.	1.6	9
78	A Wide Tuning Range CMOS Oscillator Mixer Using A Push-Push Technique for V-band Applications. Microwave and Optical Technology Letters, 2013, 55, 1934-1937.	0.9	1
79	On-chip dual-band bandpass filter on a GaAs substrate. Electronics Letters, 2013, 49, 1157-1159.	0.5	6
80	Hairpin bandpass filter on Liquid Crystal Polymer substrate using inkjet printing technology. , 2013, , .		6
81	A low LO power V-band Gilbert-cell down-conversion mixer using 90 nm CMOS technology. , 2013, , .		7
82	Development of an Electrostatic Discharge Protection Solution in GaN Technology. IEEE Electron Device Letters, 2013, 34, 1491-1493.	2.2	10
83	Low insertion loss Ka-band SPST switch using S-GCPW designs. , 2012, , .		0
84	A 3.5 GHz antiparallel diode pair mixer in GaN-on-Si HEMT technology. , 2012, , .		2
85	GaN-Based High-k Praseodymium Oxide Gate MISFETs with P2S5/(NH4)2SX+ UV Interface Treatment Technology. Active and Passive Electronic Components, 2012, 2012, 1-10.	0.3	3
86	Ultra-Wideband Circuits, Systems, and Applications. Journal of Electrical and Computer Engineering, 2012, 2012, 1-2.	0.6	0
87	The body driven low phase noise injection-locked V-band push-push complementary-Colpitts oscillator. , 2012, , .		0
88	Low-Frequency Noise in Enhancement-Mode GaN MOS-HEMTs by Using Stacked $\text{Al}_2\text{O}_3/\text{Ga}_2\text{O}_3/\text{Gd}_2\text{O}_3$ Gate Dielectric. IEEE Electron Device Letters, 2012, 33, 958-960.	2.2	24
89	High performance V-band GaAs power amplifier and low noise amplifier using low-loss transmission line technology. , 2012, , .		3
90	A fully integrated multi-band ED-mode pHEMT VCO using variable transformer and switched resonator. International Journal of Electronics, 2012, 99, 877-884.	0.9	1

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91	Quality of the Oxidation Interface of AlGaIn in Enhancement-Mode AlGaIn/GaN High-Electron Mobility Transistors. IEEE Transactions on Electron Devices, 2012, 59, 3334-3338.	1.6	32
92	A 60 GHz wide tuning range CMOS self-oscillating mixer using a push-push VCO technique. , 2012, , .		0
93	A 600 V AlGaIn/GaN Schottky barrier diode on silicon substrate with fast reverse recovery time. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 949-952.	0.8	16
94	A 30-65 GHz wideband double-balanced Gilbert cell mixer using GaAs pHEMT technology. Microwave and Optical Technology Letters, 2012, 54, 1196-1200.	0.9	5
95	Design and Analysis of a Tri-Band Dual-Mode Chip Filter for 60-, 77-, and 100-GHz Applications. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 989-997.	2.9	5
96	A Novel Self-Aligned Raised Source/Drain Polysilicon Thin-Film Transistor With a High-Current Structure. IEEE Electron Device Letters, 2011, 32, 1080-1082.	2.2	4
97	A high protection voltage dual-gate GaN HEMT clamp for electric vehicle application. , 2011, , .		3
98	Characterization of enhancement-mode AlGaIn/GaN high electron mobility transistor using N <sub>2</sub> O plasma oxidation technology. Applied Physics Letters, 2011, 99, 153508.	1.5	23
99	28-GHz patch antenna arrays with PCB and LTCC substrates. , 2011, , .		25
100	Development of a New pHEMT-Based Electrostatic Discharge Protection Structure. IEEE Transactions on Electron Devices, 2011, 58, 2974-2980.	1.6	12
101	A K-band balanced subharmonically pumped image rejection mixer using 0.15- $\mu$ m GaAs pHEMT technology. Microwave and Optical Technology Letters, 2011, 53, 485-488.	0.9	2
102	A Ka-band low-noise amplifier using semicircle stacked-GCPW transmission line. Microwave and Optical Technology Letters, 2011, 53, 1131-1134.	0.9	0
103	Improvement of the $Q$ -factor, for an adjustable inductor using a 90- $\mu$ m silicon substrate on plastic. International Journal of Electronics, 2011, 98, 1597-1602.	0.9	2
104	A wideband Gilbert cell mixer with an integrated Marchand balun using 0.5- $\mu$ m GaAs enhancement-mode pHEMT technology. Microwave and Optical Technology Letters, 2010, 52, 1302-1306.	0.9	0
105	Low power dual transformer injection locked frequency divider using 0.5 $\mu$ m GaAs E/D-mode PHEMTs process. Microwave and Optical Technology Letters, 2010, 52, 2302-2306.	0.9	0
106	Effect of rapid thermal annealing on Mg <sub>x</sub> Zn <sub>1-x</sub> O films prepared by radio-frequency magnetron sputtering. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 720-723.	0.6	12
107	A Wide Tuning Range 69 GHz Push-Push VCO Using 0.18 $\mu$ m CMOS Technology. IEEE Microwave and Wireless Components Letters, 2010, 20, 97-99.	2.0	29
108	An improved passive inductor microwave performance on gallium nitride substrates using ion implantation technology. International Journal of Electronics, 2010, 97, 695-701.	0.9	1

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109	Dumbbell DGS based broadband RF choke for UWB LNA. , 2010, , .		1
110	Multilayer asymmetrical compact microstrip resonator cell band-pass filter using LTCC technology. , 2010, , .		0
111	Optoelectronic Mixer Based on Composite Transparent Gate InAlAs/InGaAs Metamorphic HEMTs. Journal of Lightwave Technology, 2010, 28, 2153-2161.	2.7	6
112	An X-band ultra-low phase noise differential Colpitts voltage-controlled oscillator using 0.15 $\mu$ m pseudomorphic high electron mobility transistor technology. International Journal of Electronics, 2010, 97, 605-611.	0.9	1
113	Field-plate technique for high power compound semiconductor devices applications. , 2010, , .		0
114	Ka-band high gain low noise amplifier by Stacked-GCPW transmission line. , 2010, , .		4
115	On-State and Off-State Breakdown Voltages in GaAs PHEMTs With Various Field-Plate and Gate-Recess Extension Structures. IEEE Electron Device Letters, 2010, 31, 186-188.	2.2	8
116	A 24GHz sub-harmonically image rejection mixer with various asymmetrical diode pair. , 2010, , .		1
117	A high breakdown voltage and low switching loss GaN schottky diode using CHF. , 2010, , .		0
118	An optoelectronic mixer based on composite transparent gate InAlAs/InGaAs metamorphic HEMT. , 2010, , .		0
119	SLL similarity filling factor design for Chebyshev modulated dumbbell DGS low pass filters. , 2009, , .		5
120	Design of a Ka-band bandpass filter with asymmetrical compact resonator. , 2009, , .		4
121	A High-Linearity Single-Pole-Double-Throw Pseudomorphic HEMT Switch Based on Tunable Field-Plate Voltage Technology. IEEE Transactions on Electron Devices, 2009, 56, 541-545.	1.6	6
122	Device performance of AlGaIn/GaN MOS-HEMTs using La <sub>2</sub> O <sub>3</sub> high-k oxide gate insulator. , 2009, , .		0
123	ZnO based thin-film transistor with high- $\epsilon$ ; gadolinium and praseodymium oxide as gate dielectric. , 2009, , .		3
124	High Linearity AlGaAs/InGaAs Pseudomorphic HEMT Driver Amplifier Using Tunable Field-Plate Voltage Technology. , 2009, , .		2
125	An UWB CMOS voltage-controlled oscillator with 2-6 GHz tuning range using active inductor technology. Microwave and Optical Technology Letters, 2008, 50, 2311-2315.	0.9	3
126	Device Characteristics of AlGaIn/GaN MOS-HEMTs Using High- $\epsilon$ Praseodymium Oxide Layer. IEEE Transactions on Electron Devices, 2008, 55, 3305-3309.	1.6	22



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127	Efficiency design of a 10GHz CMOS oscillator. , 2008, , .		0
128	A Ka-Band Monolithic CPW-Mode T/R Modules Using 0.15 $\mu$ m Gate-Length GaAs pHEMT Technology. , 2008, , .		1
129	Phase-noise improvement of GaAs pHEMT K-band voltage controlled oscillator using tunable field-plate voltage technology. , 2008, , .		0
130	High thermal stability AlGaAs/InGaAs enhancement-mode pHEMT Using Pd buried-gate technology. , 2008, , .		0
131	A novel compact complementary Colpitts differential CMOS VCO with low phase-noise performance. , 2008, , .		6
132	High sensitivity pH sensor using Al <sub>x</sub> In <sub>1-x</sub> Ga <sub>1-x</sub> N/GaN HEMT heterostructure design. , 2008, , .		2
133	Phase-Noise Improvement of GaAs pHEMT K-Band Voltage-Controlled Oscillator Using Tunable Field-Plate Voltage Technology. IEEE Electron Device Letters, 2008, 29, 426-429.	2.2	3
134	A fully integrated 24 GHz sub-harmonic image rejection mixer with quadrature coupler. , 2008, , .		4
135	AZO transparent thin film with E-gun evaporate procedure and application on light emitting diode. , 2008, , .		0
136	A compact size Ka band pHEMT MMIC frequency tripler using lump element balun. , 2008, , .		1
137	A 12-GHz Low Phase Noise VCO By Employing CMOS Field-Plate Transistors. , 2007, , .		1
138	A Compact Size Ka Band pHEMT MMIC Frequency Tripler with CPW Technology. , 2007, , .		1
139	A low noise 3.1 10.6 GHz pMOS distributed amplifier for ultra-wideband applications. Microwave and Optical Technology Letters, 2007, 49, 1641-1644.	0.9	2
140	A 12-GHz Low-Phase-Noise Voltage-Controlled Oscillator Using Novel Field-Plate CMOS Transistors. IEEE Transactions on Electron Devices, 2007, 54, 2803-2807.	1.6	8
141	High breakdown voltage (Al <sub>0.3</sub> Ga <sub>0.7</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P/InGaAs quasi-enhancement-mode pHEMT with field-plate technology. IEEE Electron Device Letters, 2005, 26, 701-703.	2.2	7
142	An ultra-wideband CMOS VCO with 3-5 GHz tuning range. , 2005, , .		9
143	Novel C-band and K-band 3-D InGaP/InGaAs MMICs using low-k BCB interlayer. , 0, , .		1
144	High Linearity Performance of 0.13 $\mu$ m CMOS Devices using Field-Plate Technology. , 0, , .		0